

Electronic Supplementary Information (ESI)

Broadband near infrared persistent luminescence in Ni²⁺-doped transparent glass ceramic ZnGa₂O₄†

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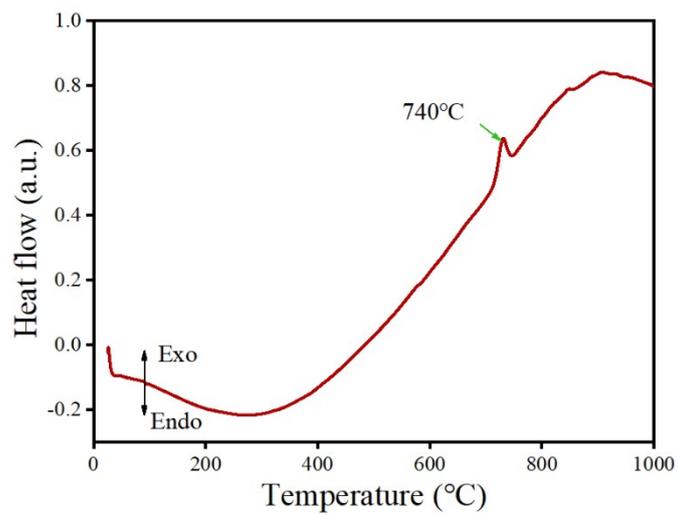


Fig. S1. DSC trace of ZnGa₂O₄:0.05Ni²⁺ PG.

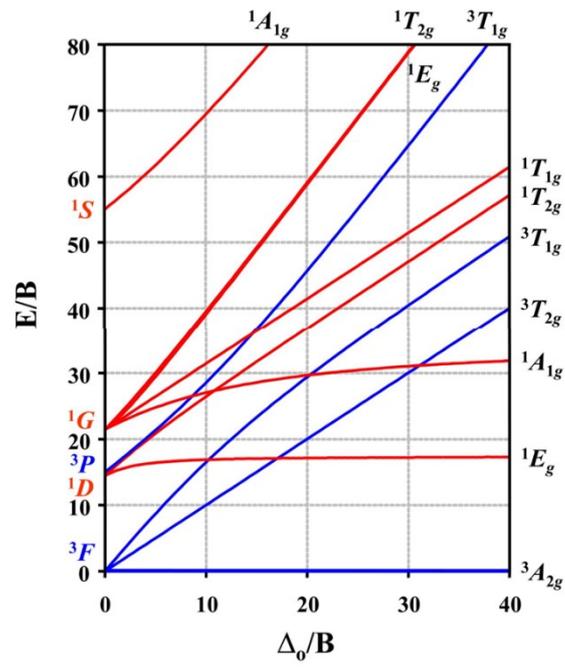


Fig. S2. Tanabe-Sugano diagram in which the straight lines indicate the crystal field of Ni²⁺ in the ZnGa₂O₄ host.

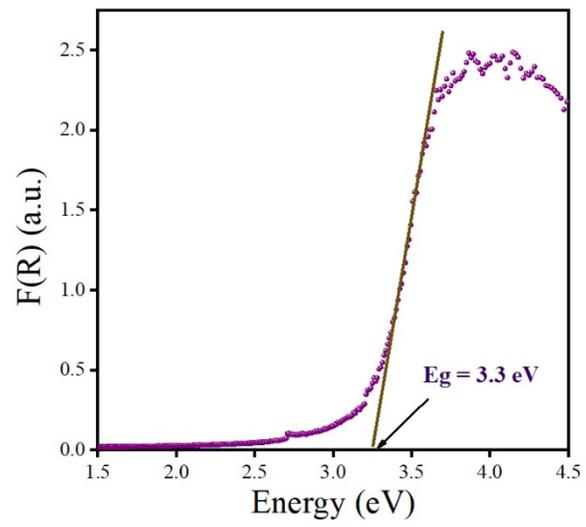


Fig. S3. The calculated bandgap of ZnGa₂O₄ host.